Li, Jiapeng

List of Publications by Year
in descending order

28	304	840776 11	940533 16
papers	citations	h-index	g-index

29	29	29	192
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A Comparative Study on Fluorination and Oxidation of Indiumâ€“Galliumâ€“Zinc Oxide Thin-Film Transistors. IEEE Electron Device Letters, 2018, 39, 196-199.	3.9	37
2	High-performance and reliable elevated-metal metal-oxide thin-film transistor for high-resolution displays. , 2016, , .		33
3	Elevated-Metal Metal-Oxide (EMMO) Thin-Film Transistor: Technology and Characteristics. IEEE Electron Device Letters, 2016, , 1-1.	3.9	30
4	Fluorination-Enabled Monolithic Integration of Enhancement- and Depletion-Mode Indium-Gallium-Zinc Oxide TFTs. IEEE Electron Device Letters, 2018, 39, 692-695.	3.9	25
5	A Comparative Study on the Effects of Annealing on the Characteristics of Zinc Oxide Thin-Film Transistors With Gate-Stacks of Different Gas-Permeability. IEEE Electron Device Letters, 2014, 35, 841-843.	3.9	24
6	An oxidation-last annealing for enhancing the reliability of indium-gallium-zinc oxide thin-film transistors. Applied Physics Letters, 2017, 110, .	3.3	24
7	Characteristics of Elevated-Metal Metal-Oxide Thin-Film Transistors Based on Indium-Tin-Zinc Oxide. IEEE Electron Device Letters, 2017, 38, 894-897.	3.9	19
8	Resilience of Fluorinated Indium-Gallium-Zinc Oxide Thin-Film Transistor Against Hydrogen-Induced Degradation. IEEE Electron Device Letters, 2020, 41, 729-732.	3.9	17
9	A Physical Model for Metalâ€“Oxide Thin-Film Transistor Under Gate-Bias and Illumination Stress. IEEE Transactions on Electron Devices, 2018, 65, 142-149.	3.0	15
10	A Bottom-Gate Metalâ€“Oxide Thin-Film Transistor With Self-Aligned Source/Drain Regions. IEEE Transactions on Electron Devices, 2018, 65, 2820-2826.	3.0	15
11	Pâ€15: The Use of Fluorination to Enhance the Performance and the Reliability of Elevatedâ€Metal Metalâ€Oxide Thinâ€Film Transistors. Digest of Technical Papers SID International Symposium, 2018, 49, 1235-1238.	0.3	14
12	Thermally Induced Variation of the Turn-ON Voltage of an Indiumâ€“Galliumâ€“Zinc Oxide Thin-Film Transistor. IEEE Transactions on Electron Devices, 2015, 62, 3703-3708.	3.0	13
13	Self-Aligned Elevated-Metal Metal-Oxide Thin-Film Transistors for Displays and Flexible Electronics. , 2019, , .		11
14	Fluorinated indiumâ€galliumâ€zinc oxide thinâ€film transistor with reduced vulnerability to hydrogenâ€induced degradation. Journal of the Society for Information Display, 2020, 28, 520-527.	2.1	10
15	Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor With Self-Aligned Definition of the Active Island. IEEE Electron Device Letters, 2018, 39, 35-38.	3.9	5
16	24â€2: Distinguished Student Paper: Fluorination for Enhancing the Resistance of Indiumâ€Galliumâ€Zinc Oxide Thinâ€Film Transistor against Hydrogenâ€Induced Degradation. Digest of Technical Papers SID International Symposium, 2020, 51, 347-350.	0.3	3
17	8.1: Invited Paper: Enhanced Elevatedâ€Metal Metalâ€Oxide Thinâ€Film Transistor Technology. Digest of Technical Papers SID International Symposium, 2018, 49, 75-78.	0.3	2
18	Pâ€11: Carrier Concentration Reduction by Fluorine Doping in Pâ€Type SnO Thinâ€Film Transistors. Digest of Technical Papers SID International Symposium, 2019, 50, 1251-1254.	0.3	2

#	Article	IF	Citations
19	A Timing Model for the Optimal Design of a Prototype Active-Matrix Display. IEEE Transactions on Electron Devices, 2020, 67, 3167-3174.	3.0	2
20	Pâ€1.5: Edge Effects of Threeâ€Mask Elevatedâ€Metal Metalâ€Oxide Thinâ€Film Transistor and Their Elimination. Digest of Technical Papers SID International Symposium, 2018, 49, 531-534.	0.3	1
21	1.3: A Timing Model for the Design of an Activeâ€Matrix Display. Digest of Technical Papers SID International Symposium, 2019, 50, 13-16.	0.3	1
22	Pâ€4: Enhanced Scalability and Reliability of High Mobility Elevatedâ€Metal Metalâ€Oxide Thinâ€Film Transistors with Bandgap Engineering. Digest of Technical Papers SID International Symposium, 2020, 51, 1322-1325.	0.3	1
23	Elevated metal metal-oxide thin-film transistor â€" A new bottom-gate transistor architecture for flat-panel displays. , 2016, , .		0
24	Pâ€1.4: Elevatedâ€Metal Metalâ€Oxide Thinâ€Film Transistor with Fluorinated Indiumâ€Galliumâ€Zinc Oxide Channel towards Flexible Applications. Digest of Technical Papers SID International Symposium, 2018, 49, 528-530.	0.3	0
25	24.3: Shortâ€Channel Indiumâ€Galliumâ€Zinc Oxide Thinâ€Film Transistor Enabled by Thermal Dehydrogenation and Oxidizing Defectâ€Suppression. Digest of Technical Papers SID International Symposium, 2018, 49, 255-258.	0.3	0
26	Pâ€21: Threeâ€Mask Elevatedâ€Metal Metalâ€Oxide Thinâ€Film Transistor Technology for Highâ€Resolution AMOLED Application. Digest of Technical Papers SID International Symposium, 2018, 49, 1256-1259.	0.3	0
27	8.2: Invited Paper: Elevatedâ€Metal Metalâ€Oxide Thinâ€Film Transistor with Selfâ€Aligned Source/Drain Regions. Digest of Technical Papers SID International Symposium, 2019, 50, 75-78.	0.3	0
28	Systematic Defect Manipulation in Metal Oxide Semiconductors towards High-Performance Thin-Film Transistors. , 2020, , .		0